THIN FILM TRANSISTOR TECHNOLOGIES (TFTT VII)

Proceedings of the International Symposium

Editor

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PREFACE

This proceedings volume contains papers presented at the Seventh Symposium on Thin Film Transistor Technologies (TFTT VII), held in Honolulu, Hawaii, USA, October 4-6, 2004. This symposium was sponsored by the Electronics and Dielectric Science and Technologies Divisions of The Electrochemical Society.

This symposium was organized into 9 sections: Poly-Si TFTs from Laser Crystallization, Poly-Si TFTs from Metal-and Non-Metal-Induced Crystallization, TFT Gate Dielectrics, Doping, Structures, etc., Devices and Modeling, Circuits and Systems, Materials and Substrates, Organic TFTs, New and Novel Applications, and Posters. Totally, 39 papers contributed from 13 countries or regions, i.e., Brazil, Canada, China, France, Germany, Greece, Hong Kong, Japan, Korea, Netherlands, Spain, Taiwan, UK and USA, are included in this proceedings volume. Authors are from industry/institutes (Advanced LCD Technologies Development Center Co., Corning, DuPont, FlexICs, Fujitsu, Hitachi, IBM, Japan Science & Technology Agency, NEC, Optoelectronic Industry and Technology Development Assoc., Philips, Samsung, Seiko Epson, and Sharp) and universities (Aristotle University of Thessaloniki, Cambridge University, Delft University of Technology, Hanyang University, Hong Kong University of Science and Technology, Kyung Hee University, Lehigh University, Nankai University, National and Kapodistrian University of Athens, National Chiao-Tung University, Norwegian University of Science and Technology, Pennsylvania State University, Rennes I University, Rensselaer Polytechnic Institute, Sejong University, Shimane University, Seoul National University, Simon Fraser University, Sungkyunkwan University, Surrey University, Technische Universitat Dresden, Texas A&M University, Tokyo University, Tokyo Institute of Technology, Tokyo Polytechnic University, and Universitat Rovira i Virgili).

In order to present all papers in a coherent manner, this proceedings volume is edited into 8 sections. All papers are published as their original forms without alteration of their technical contents except for the format.

The editor wishes to express his sincere appreciation to the following people for their involvement in organizing and conducting the symposium:

- co-organizers for their contributions in planning and coordinating the program.
- authors and presenters of papers for their participation.
- section chairs and co-chairs for their conducting the meeting.
- B. Bachetti for his assistance in preparing and editing the volume.
- staffs of The Electrochemical Society for their administrative assistance in organizing the symposium and in publishing this volume.

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# TABLE OF CONTENTS

**PREFACE**

**Poly-Si TFTs from Laser Crystallization Methods**

- CW Laser Lateral Crystallization (CLC)*  
  N. Sasaki  
  1

- Novel Phase-Modulator for ELA-Based Lateral Growth of Si  
  Y. Taniguchi, M. Jyomonji, H. Ogawa, M. Hiramatsu, and M. Matsumura  
  18

- An Advanced Sample Structure for Excimer Laser Crystallization  
  M. Hiramatsu, H. Ogawa, M. Jyomonji, T. Katou, N. Akita, and M. Matsumura  
  30

- The Electrical Characteristics of the Poly-Si TFTs fabricated by 2-Dimensional Grain Growing ELA method  
  I.-H. Song, H.-S. Shin, and M.-K. Han  
  38

- A New Dual L-Gate Structure of Poly-Si TFT for Suppressing the Kink Effect in SLS/CW Laser Method  
  S.-H. Jung, H.-S. Shin, and M.-K. Han  
  44

**Poly-Si TFTs from Non Laser Crystallization Methods**

- Reliability Study of MILC Poly-Si TFTs on Plastic Substrates Using PostFlex Transfer Process  
  H. Li and S. Fonash  
  49

- Reduction of the Leakage Current of Thin-Film Transistor on Metal-Induced Laterally Crystallized Polycrystalline Silicon  
  Z. Meng, C. Wu, S. Xiong, X. Shi, H.S. Kwok, and M. Wong  
  57

**TFTs Gate Dielectrics, Doping, Structures, etc.**

- Low-Temperature Microwave Plasma Oxidation for Gate Dielectrics of Poly-Si TFTs using High-Density Surface Wave Plasma*  
  K. Azuma  
  63

- Fabrication and characterization of n- and p-channel poly-Si TFTs by sputtering deposition of ultra thin gate SiO2 films  
  T. Serikawa, M. Miyashita, Y. Uraoka, and T. Fuyuki  
  74

- Ion Shower Doping of Polysilicon Films on Plastic Substrates for Flexible TFT Arrays  
  80

* Invited Paper
<table>
<thead>
<tr>
<th>Title</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>A Simple CMOS Self-Aligned Double-Gate Poly-Si TFT Technology</td>
<td>87</td>
</tr>
<tr>
<td>Z. Xiong, H. Liu, C. Zhu, and J. K. O. Sin</td>
<td></td>
</tr>
<tr>
<td>Influence of Channel Position on Characteristics of p-Channel c-Si TFT Inside a Location-Controlled Grain</td>
<td>92</td>
</tr>
<tr>
<td>High Performance P-Channel Schottky Barrier Thin-Film Transistors with PtSi Source/Drain</td>
<td>99</td>
</tr>
<tr>
<td>M.-H. Lee, T.-Y. Huang, K.-L. Yeh, and H.-C. Lin</td>
<td></td>
</tr>
<tr>
<td>Devices and Modeling</td>
<td></td>
</tr>
<tr>
<td>Hot-Carrier Instability in N- and P-Channel Poly-Si Tofts*</td>
<td>104</td>
</tr>
<tr>
<td>H. Tango, M. Suganuma, G. Usami and Y. Nogami</td>
<td></td>
</tr>
<tr>
<td>Switch-on Undershoot Current Observed in Thin Film Transistors</td>
<td>112</td>
</tr>
<tr>
<td>F. Yan, P. Migliorato, and R. Ishihara</td>
<td></td>
</tr>
<tr>
<td>Modelling of Source Gated Transistors in Amorphous Silicon</td>
<td>119</td>
</tr>
<tr>
<td>F. Balon and J. M. Shannon</td>
<td></td>
</tr>
<tr>
<td>An Investigation of the Electrically Active Defects in poly-Si Thin Film Transistors</td>
<td>125</td>
</tr>
<tr>
<td>M. Exarchos, G. J. Papaioannou, D. N. Kouvatsos, and A. T.Voutsas</td>
<td></td>
</tr>
<tr>
<td>Simulation of Twin Boundary Effect on TFT Characteristics</td>
<td>130</td>
</tr>
<tr>
<td>Y. Mo, F. Yan, P. Migliorato, and R. Ishihara</td>
<td></td>
</tr>
<tr>
<td>Circuits and Systems</td>
<td></td>
</tr>
<tr>
<td>Thin Film Transistor Models for Circuit Simulation*</td>
<td>136</td>
</tr>
<tr>
<td>B. Iñiguez, M. S. Shur, T. A. Fjeldly, and T. Ytterdal</td>
<td></td>
</tr>
<tr>
<td>TFT Mobility Requirement for AMOLED HDTVs*</td>
<td>146</td>
</tr>
<tr>
<td>O.-K. Kwon</td>
<td></td>
</tr>
<tr>
<td>System Displays and TFT Device and Process Technologies*</td>
<td>159</td>
</tr>
<tr>
<td>H. Abe</td>
<td></td>
</tr>
<tr>
<td>High Performance TFT Circuits for all-Integrated Systems on Stainless Steel Foils</td>
<td>166</td>
</tr>
</tbody>
</table>

* Invited Paper
Materials and Substrates

Oxide Semiconductors for Flexible Electronics*
P. F. Garcia, R. S. McLean, I. Malajovich, and M. H. Reilly 178

Thin-Film Transistors Based on Spin-Coated Chalcogenide Semiconductor Channels*
D. B. Mitzi, M. Copel, C. E. Murray, L. Kosbar, and A. Afzali 189

Hydrogen-Induced Defects in Poly-Silicon Thin Films Observed by Raman Spectroscopy
K. Kitahara, Y. Ohashi, T. Yamada, and A. Moritani 200

Analysis of Transfer Mechanism in Surface Free Technology by Laser Annealing / Ablation (SUFTLA)*
S. Inoue, M. Kasuga, S. Utsunomiya, and T. Shimoda 206

High Mobility Top-Gate Micro-Crystalline Silicon TFTs Processed at Low Temperature (<200°C)
A. Saboundji, N. Coulon, C. Simon, T. Mohammed-Brahim, O. Bonnaud 215

Polysilicon TFTs on Plastic
J. Y. Chen 221

VHF PECVD Micro-crystalline Silicon Bottom Gate TFT With Thin Incubation Layer

Organic TFTs

Semicconducting Properties of Pentacene Thin Films Studied by Complex Impedance, Surface Mobility and Photo-induced Effects*
A. Toriumi, T. Yokoyama, T. Nishimura, T. Yamada, K. Kita, and K. Kyuno 237

Bottom Contact Organic Thin-Film Transistors with Thiol-based SAM Treatment
M. Kawasaki, S. Imazeki, M. Ando, and M. Ohe 249

Flexible QVGA Active Matrix Displays based on Organic Electronics*
F. J. Touwslager, H.E.A. Huitema, G. H. Gelinck, E. van Veenendaal, and P.J. G. van Lieshout 257

Study of Organic Field-Effect Transistors from Poly-3-octylthiophene Solutions on Different Gate Dielectrics
A Novel TFT-Driven Microchannel Electrophoresis Device for Proteins Separation and Identification
Y. Kuo and H. H. Lee

Hydrogenated Amorphous Silicon Bipolar Junction Thin Film Transistors (a-Si:H B-TFTs)
Y. Lei, Y. Kuo, and H. Nominanda

Highly pH Sensitive Suspended-Gate Silicon Thin Film Transistor (ISTFT)
F. Bendriaa, F. Le Bihan, A.-C. Salaün, T. Mohammed-Brahim, and O. Bonnaud

High Dynamic Range Pixel Amplifier Architecture in Amorphous Silicon Technology for Diagnostic X-ray Imaging Applications
G. Sanaie-Fard, R Sanaie-Fard, and K.S. Karim

New Pixel Circuit to Recover Threshold Voltage Shift in Amorphous Silicon TFT for Active Matrix OLEDs

Low-Temperature Deposition of Poly-Si and SiGe Thin Films at 450°C and Fabrication of High Mobility TFTs Over 50 CM²/VS

AUTHOR INDEX

SUBJECT INDEX